INTEGRATED CIRCUITS

DATA SHEET

74LVC1G80Single D-type flip-flop; positive-edge trigger

Product specification
File under Integrated Circuits, IC24

2001 Apr 04





Single D-type flip-flop; positive-edge trigger

74LVC1G80

FEATURES

- Wide supply voltage range from 1.65 to 5.5 V
- · High noise immunity
- Complies with JEDEC standard:
 - JESD8-7 (1.65 to 1.95 V)
 - JESD8-5 (2.3 to 2.7 V)
 - JESD8B/JESD36 (2.7 to 3.6 V).
- ±24 mA output drive (V_{CC} = 3.0 V)
- CMOS low power consumption
- Latch-up performance ≤250 mA
- · Direct interface with TTL levels
- · SOT353 package.

DESCRIPTION

The 74LVC1G80 is a high-performance, low-power, low-voltage, Si-gate CMOS device, superior to most advanced CMOS compatible TTL families.

Inputs can be driven from either 3.3 or 5 V devices. This feature allows the use of this device in a mixed 3.3 and 5 V environment.

This device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

The 74LVC1G80 provides a single positive-edge triggered D-type flip-flop.

Information on the data input is transferred to the $\overline{\mathbb{Q}}$ output on the LOW-to-HIGH transition of the clock pulse. The D input must be stable one set-up time prior to the LOW-to-HIGH clock transition for predictable operation.

QUICK REFERENCE DATA

GND = 0 V; $T_{amb} = 25 \, ^{\circ}\text{C}$; $t_r = t_f \le 2.5 \, \text{ns}$.

SYMBOL	PARAMETER	CONDITIONS	TYPICAL	UNIT
t _{PHL} /t _{PLH}	propagation delay CP to Q	$V_{CC} = 1.8 \text{ V}; C_L = 30 \text{ pF}; R_L = 1 \text{ k}\Omega$	3.4	ns
		$V_{CC} = 2.5 \text{ V}; C_L = 30 \text{ pF}; R_L = 500 \Omega$	2.3	ns
		$V_{CC} = 3.3 \text{ V}; C_L = 50 \text{ pF}; R_L = 500 \Omega$	2.4	ns
		$V_{CC} = 5.0 \text{ V}; C_L = 50 \text{ pF}; R_L = 500 \Omega$	1.8	ns
Cı	input capacitance		5	pF
C _{PD}	power dissipation capacitance per buffer	V _{CC} = 3.3 V; notes 1	17	pF

Note

1. C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i + (C_L \times V_{CC}^2 \times f_o)$ where:

 f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in Volts.

Single D-type flip-flop; positive-edge trigger

74LVC1G80

FUNCTION TABLE

See note 1.

INF	OUTPUT	
СР	D	Q
↑	L	Н
↑	Н	L
L	X	\overline{q}

Note

1. H = HIGH voltage level;

L = LOW voltage level;

↑ = LOW-to-HIGH CP transition;

X = don't care;

 \overline{q} = lower case letter indicates the state of referenced input, one set-up time prior to the LOW-to-HIGH CP transition.

ORDERING INFORMATION

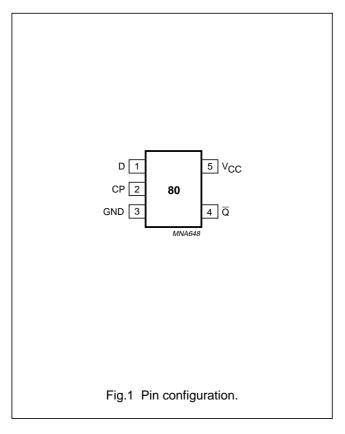
	PACKAGE							
TYPE NUMBER	TEMPERATURE RANGE	PINS	PACKAGE	MATERIAL	CODE	MARKING		
74LVC1G80GW	–40 to +85 °C	5	SC-88A	plastic	SOT353	VT		

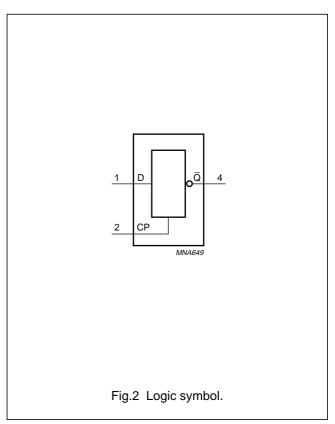
PINNING

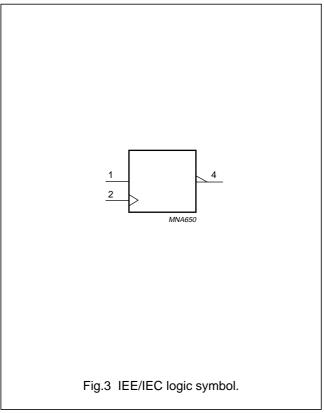
PIN	SYMBOL	DESCRIPTION
1	D	data input D
2	СР	clock pulse input CP
3	GND	ground (0 V)
4	Q	data output Q
5	V _{CC}	supply voltage

Single D-type flip-flop; positive-edge trigger

74LVC1G80

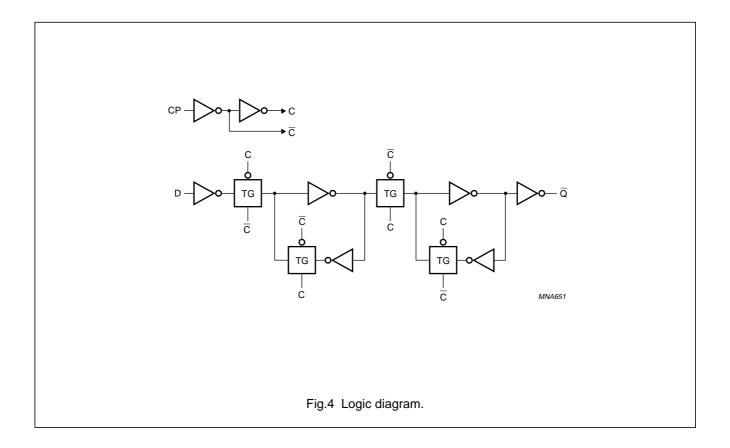






Single D-type flip-flop; positive-edge trigger

74LVC1G80



Single D-type flip-flop; positive-edge trigger

74LVC1G80

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CC}	supply voltage		1.65	5.5	V
VI	input voltage		0	5.5	V
Vo	output voltage	active mode	0	V _{CC}	V
		Power-down mode; V _{CC} = 0 V	0	5.5	V
T _{amb}	operating ambient temperature		-40	+85	°C
t _r , t _f	input rise and fall times	V _{CC} = 1.65 to 2.7 V	0	20	ns/V
		V _{CC} = 2.7 to 5.5 V	0	10	ns/V

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134); voltages are referenced to GND (ground = 0 V).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CC}	supply voltage		-0.5	+6.5	V
I _{IK}	input diode current	V _I < 0	_	-50	mA
VI	input voltage	note 1	-0.5	+6.5	V
I _{OK}	output diode current	$V_O > V_{CC}$ or $V_O < 0$	_	±50	mA
Vo	output voltage	active mode; notes 1 and 2	-0.5	V _{CC} + 0.5	V
		Power-down mode; notes 1 and 2	-0.5	+6.5	V
Io	output diode current	$V_O = 0$ to V_{CC}	_	±50	mA
I _{CC} , I _{GND}	V _{CC} or GND current		_	±100	mA
T _{stg}	storage temperature		-65	+150	°C
P _D	power dissipation per package	for temperature range from –40 to +85 °C; note 3	_	200	mW

Notes

- 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
- 2. When V_{CC} is powered-down to 0 V, the output voltage can be 5.5 V in normal operation.
- 3. Above 55 $^{\circ}$ C the value of P_D derates linearly with 2.5 mW/K.

Single D-type flip-flop; positive-edge trigger

74LVC1G80

DC CHARACTERISTICS

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

		TEST CONDITION	,				
SYMBOL	PARAMETER			-40 to +85			UNIT
		OTHER	V _{CC} (V)	MIN.	TYP. ⁽¹⁾	MAX.	<u> </u>
V _{IH}	HIGH-level input		1.65 to 1.95	$0.65 \times V_{CC}$	_	_	V
	voltage		2.3 to 2.7	1.7	_	_	V
			2.7 to 3.6	2.0	_	_	٧
			4.5 to 5.5	$0.7 \times V_{CC}$	_	_	V
V_{IL}	LOW-level input		1.65 to 1.95	_	_	$0.35 \times V_{CC}$	V
	voltage		2.3 to 2.7	_	_	0.7	٧
			2.7 to 3.6	_	_	0.8	٧
			4.5 to 5.5	_	_	$0.3 \times V_{CC}$	V
V _{OL}	LOW-level output	$V_I = V_{IH}$ or V_{IL} ; $I_O = 100 \mu A$	1.65 to 5.5	_	_	0.1	V
	voltage	$V_I = V_{IH}$ or V_{IL} ; $I_O = 4$ mA	1.65	_	_	0.45	V
		$V_I = V_{IH}$ or V_{IL} ; $I_O = 8$ mA	2.3	_	_	0.3	٧
		$V_I = V_{IH}$ or V_{IL} ; $I_O = 12$ mA	2.7	_	_	0.4	V
		$V_I = V_{IH}$ or V_{IL} ; $I_O = 24$ mA	3.0	_	_	0.55	V
		$_{\rm I}V = V_{\rm IH}$ or $V_{\rm IL}$; $I_{\rm O} = 32$ mA	4.5	_	_	0.55	٧
V _{OH}	HIGH-level output	$V_I = V_{IH}$ or V_{IL} ; $I_O = -100 \mu A$	1.65 to 5.5	V _{CC} - 0.1	_	_	٧
	voltage	$V_I = V_{IH}$ or V_{IL} ; $I_O = -4$ mA	1.65	1.2	_	_	٧
		$V_I = V_{IH}$ or V_{IL} ; $I_O = -8$ mA	2.3	1.9	_	_	٧
		$V_I = V_{IH}$ or V_{IL} ; $I_O = -12$ mA	2.7	2.2	_	_	٧
		$V_I = V_{IH}$ or V_{IL} ; $I_O = -24$ mA	3.0	2.3	_	_	٧
		$V_I = V_{IH}$ or V_{IL} ; $I_O = -32$ mA	4.5	3.8	_	_	٧
ILI	input leakage current	V _I = 5.5 V or GND	3.6	_	±0.1	±5	μΑ
I _{off}	power OFF leakage current	V_I or $V_O = 5.5 \text{ V}$	0	_	±0.1	±10	μΑ
I _{CC}	quiescent supply current	$V_I = V_{CC}$ or GND; $I_O = 0$	5.5	_	0.1	10	μΑ
Δl _{CC}	additional quiescent supply current per input pin	$V_I = V_{CC} - 0.6 \text{ V}; I_O = 0$	2.3 to 5.5	-	5	500	μА

Note

1. All typical values are measured at V_{CC} = 3.3 V and T_{amb} = 25 $^{\circ}C.$

Single D-type flip-flop; positive-edge trigger

74LVC1G80

AC CHARACTERISTICS

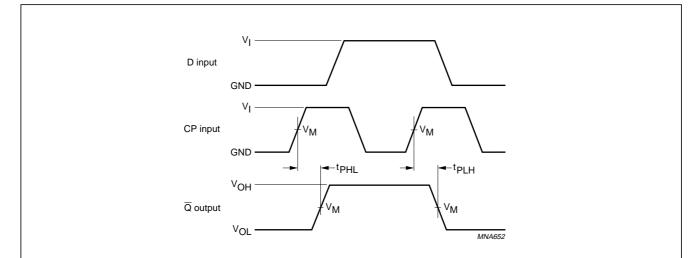
GND = 0 V; t_r = $t_f \le 2.0$ ns; unless otherwise specified.

		TEST CONI	T _{amb} (°C)				
SYMBOL	PARAMETER	WW. EEODIG		−40 to +85			UNIT
		WAVEFORMS	V _{CC} (V)	MIN.	TYP.	MAX.	
t _{PHL} /t _{PLH}	propagation delay CP to Q	see Figs 5 and 7	1.65 to 1.95	1.0	3.4	9.9	ns
			2.3 to 2.7	0.5	2.3	7.0	ns
			2.7	0.5	2.5	6.0	ns
			3.0 to 3.6	0.5	2.4	5.2	ns
			4.5 to 5.5	0.5	1.8	4.5	ns
t _{su}	set-up time D to CP	see Figs 6 and 7	1.65 to 1.95	3.0	0.8	_	ns
			2.3 to 2.7	2.5	0.6	_	ns
			2.7	2.5	0.5	_	ns
			3.0 to 3.6	2.0	0.4	_	ns
			4.5 to 5.5	2.0	0.5	_	ns
t _h	hold time D to CP	see Figs 6 and 7	1.65 to 1.95	0	-0.6	_	ns
			2.3 to 2.7	0	-0.4	_	ns
			2.7	0.5	-0.2	_	ns
			3.0 to 3.6	0.5	0.2	_	ns
			4.5 to 5.5	0.5	-0.1	_	ns
t _W	clock pulse with HIGH or LOW	see Figs 6 and 7	1.65 to 1.95	3.0	1.1	_	ns
			2.3 to 2.7	2.5	0.7	_	ns
			2.7	2.5	0.6	_	ns
			3.0 to 3.6	2.5	0.6	_	ns
			4.5 to 5.5	2.0	0.5	_	ns
f _{max}	maximum clock pulse	see Figs 6 and 7	1.65 to 1.95	100	300	_	MHz
	frequency		2.3 to 2.7	150	350	_	MHz
			2.7	150	300	_	MHz
			3.0 to 3.6	150	450	_	MHz
			4.5 to 5.5	200	500	_	MHz

Single D-type flip-flop; positive-edge trigger

74LVC1G80

AC WAVEFORMS



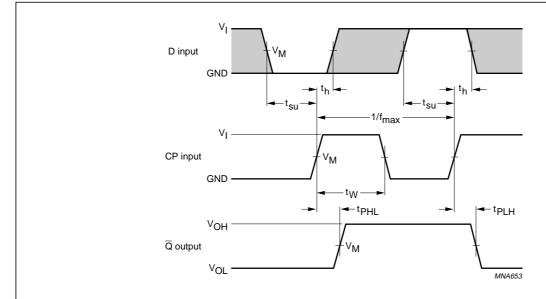
V	V	INPUT			
V CC	V _{CC} V _M		$t_r = t_f$		
1.65 to 1.95 V	$0.5 \times V_{CC}$	V _{CC}	≤ 2.0 ns		
2.3 to 2.7 V	$0.5 \times V_{CC}$	V _{CC}	≤ 2.0 ns		
2.7 V	1.5 V	2.7 V	≤ 2.5 ns		
3.0 to 3.6 V	1.5 V	2.7 V	≤ 2.5 ns		
4.5 to 5.5 V	$0.5 \times V_{CC}$	V _{CC}	≤ 2.5 ns		

 V_{OL} and V_{OH} are typical output voltage drop that occur with the output load.

Fig.5 Clock CP to output $\overline{\mathbf{Q}}$ propagation delay times.

Single D-type flip-flop; positive-edge trigger

74LVC1G80



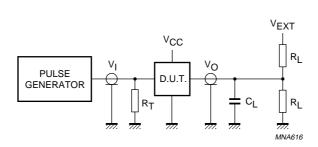
V	V	INPUT			
VCC	V _{CC} V _M		$t_r = t_f$		
1.65 to 1.95 V	$0.5 \times V_{CC}$	V _{CC}	≤ 2.0 ns		
2.3 to 2.7 V	$0.5 \times V_{CC}$	V _{CC}	≤ 2.0 ns		
2.7 V	1.5 V	2.7 V	≤ 2.5 ns		
3.0 to 3.6 V	1.5 V	2.7 V	≤ 2.5 ns		
4.5 to 5.5 V	$0.5 \times V_{CC}$	V _{CC}	≤ 2.5 ns		

The shaded areas indicate when the input is permitted to change for predictable output performance. V_{OL} and V_{OH} are typical output voltage drop that occur with the output load.

Fig.6 Clock (CP) to output (\overline{Q}) propagation delays, clock pulse width, D to CP set-up times, the D to CP hold times and maximum clock pulse frequency.

Single D-type flip-flop; positive-edge trigger

74LVC1G80



V	V _I	_	В	V _{EXT}			
V _{CC}	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	CL	R _L	t _{PLH} /t _{PHL}	t _{PZH} /t _{PHZ}	t _{PZL} /t _{PLZ}	
1.65 to 1.95 V	V _{CC}	30 pF	1 kΩ	open	GND	$2 \times V_{CC}$	
2.3 to 2.7 V	V _{CC}	30 pF	500 Ω	open	GND	$2 \times V_{CC}$	
2.7 V	2.7 V	50 pF	500 Ω	open	GND	6 V	
3.0 to 3.6 V	2.7 V	50 pF	500 Ω	open	GND	6 V	
4.5 to 5.5 V	V _{CC}	50 pF	500 Ω	open	GND	$2 \times V_{CC}$	

Definitions for test circuit:

R_L = Load resistor.

 C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance should be equal to the output impedance Z_0 of the pulse generator.

Fig.7 Load circuitry for switching times.

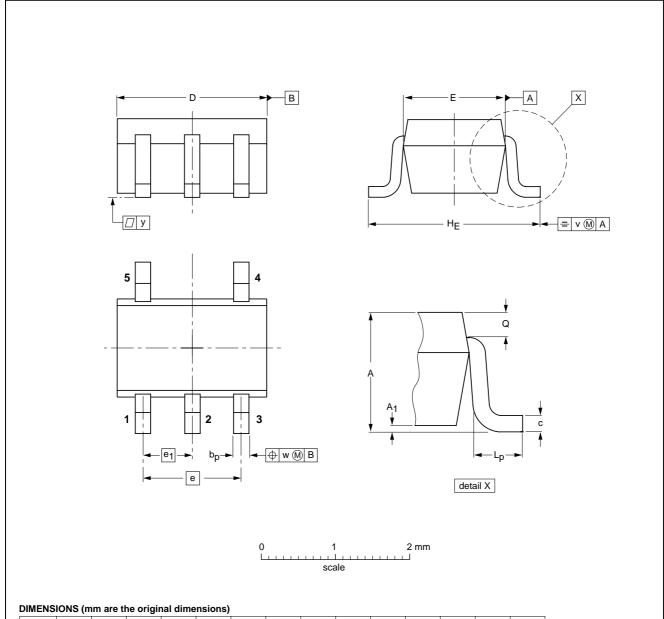
Single D-type flip-flop; positive-edge trigger

74LVC1G80

PACKAGE OUTLINE

Plastic surface mounted package; 5 leads

SOT353



D	,	 	.u. u	,	
					ī

UNIT	A	A ₁ max	bp	С	D	E ⁽²⁾	е	e ₁	HE	Lp	Q	V	w	у
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE	
SOT353			SC-88A			97-02-28	

2001 Apr 04 12

Single D-type flip-flop; positive-edge trigger

74LVC1G80

SOLDERING

Introduction to soldering surface mount packages

This text gives a very brief insight to a complex technology. A more in-depth account of soldering ICs can be found in our "Data Handbook IC26; Integrated Circuit Packages" (document order number 9398 652 90011).

There is no soldering method that is ideal for all surface mount IC packages. Wave soldering can still be used for certain surface mount ICs, but it is not suitable for fine pitch SMDs. In these situations reflow soldering is recommended.

Reflow soldering

Reflow soldering requires solder paste (a suspension of fine solder particles, flux and binding agent) to be applied to the printed-circuit board by screen printing, stencilling or pressure-syringe dispensing before package placement.

Several methods exist for reflowing; for example, convection or convection/infrared heating in a conveyor type oven. Throughput times (preheating, soldering and cooling) vary between 100 and 200 seconds depending on heating method.

Typical reflow peak temperatures range from 215 to 250 °C. The top-surface temperature of the packages should preferable be kept below 220 °C for thick/large packages, and below 235 °C for small/thin packages.

Wave soldering

Conventional single wave soldering is not recommended for surface mount devices (SMDs) or printed-circuit boards with a high component density, as solder bridging and non-wetting can present major problems.

To overcome these problems the double-wave soldering method was specifically developed.

If wave soldering is used the following conditions must be observed for optimal results:

- Use a double-wave soldering method comprising a turbulent wave with high upward pressure followed by a smooth laminar wave.
- For packages with leads on two sides and a pitch (e):
 - larger than or equal to 1.27 mm, the footprint longitudinal axis is preferred to be parallel to the transport direction of the printed-circuit board;
 - smaller than 1.27 mm, the footprint longitudinal axis must be parallel to the transport direction of the printed-circuit board.

The footprint must incorporate solder thieves at the downstream end.

 For packages with leads on four sides, the footprint must be placed at a 45° angle to the transport direction of the printed-circuit board. The footprint must incorporate solder thieves downstream and at the side corners.

During placement and before soldering, the package must be fixed with a droplet of adhesive. The adhesive can be applied by screen printing, pin transfer or syringe dispensing. The package can be soldered after the adhesive is cured.

Typical dwell time is 4 seconds at 250 °C. A mildly-activated flux will eliminate the need for removal of corrosive residues in most applications.

Manual soldering

Fix the component by first soldering two diagonally-opposite end leads. Use a low voltage (24 V or less) soldering iron applied to the flat part of the lead. Contact time must be limited to 10 seconds at up to 300 °C.

When using a dedicated tool, all other leads can be soldered in one operation within 2 to 5 seconds between 270 and 320 $^{\circ}$ C.

Single D-type flip-flop; positive-edge trigger

74LVC1G80

Suitability of surface mount IC packages for wave and reflow soldering methods

PACKAGE	SOLDERING METHOD			
PACKAGE	WAVE	REFLOW ⁽¹⁾		
BGA, LFBGA, SQFP, TFBGA	not suitable	suitable		
HBCC, HLQFP, HSQFP, HSOP, HTQFP, HTSSOP, SMS	not suitable(2)	suitable		
PLCC ⁽³⁾ , SO, SOJ	suitable	suitable		
LQFP, QFP, TQFP	not recommended ⁽³⁾⁽⁴⁾	suitable		
SSOP, TSSOP, VSO	not recommended ⁽⁵⁾	suitable		

Notes

- 1. All surface mount (SMD) packages are moisture sensitive. Depending upon the moisture content, the maximum temperature (with respect to time) and body size of the package, there is a risk that internal or external package cracks may occur due to vaporization of the moisture in them (the so called popcorn effect). For details, refer to the Drypack information in the "Data Handbook IC26; Integrated Circuit Packages; Section: Packing Methods".
- 2. These packages are not suitable for wave soldering as a solder joint between the printed-circuit board and heatsink (at bottom version) can not be achieved, and as solder may stick to the heatsink (on top version).
- 3. If wave soldering is considered, then the package must be placed at a 45° angle to the solder wave direction. The package footprint must incorporate solder thieves downstream and at the side corners.
- 4. Wave soldering is only suitable for LQFP, TQFP and QFP packages with a pitch (e) equal to or larger than 0.8 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.65 mm.
- 5. Wave soldering is only suitable for SSOP and TSSOP packages with a pitch (e) equal to or larger than 0.65 mm; it is definitely not suitable for packages with a pitch (e) equal to or smaller than 0.5 mm.

Single D-type flip-flop; positive-edge trigger

74LVC1G80

DATA SHEET STATUS

DATA SHEET STATUS(1)	PRODUCT STATUS ⁽²⁾	DEFINITIONS				
Objective data	Development	This data sheet contains data from the objective specification for production development. Philips Semiconductors reserves the right to change the specification in any manner without notice.				
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.				
Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Changes will be communicated according to the Customer Product/Process Change Notification (CPCN) procedure SNW-SQ-650A.				

Notes

- 1. Please consult the most recently issued data sheet before initiating or completing a design.
- 2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.

DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information — Applications that are described herein for any of these products are for illustrative purposes only. Philips Semiconductors make no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

DISCLAIMERS

Life support applications — These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips Semiconductors customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips Semiconductors for any damages resulting from such application.

Right to make changes — Philips Semiconductors reserves the right to make changes, without notice, in the products, including circuits, standard cells, and/or software, described or contained herein in order to improve design and/or performance. Philips Semiconductors assumes no responsibility or liability for the use of any of these products, conveys no licence or title under any patent, copyright, or mask work right to these products, and makes no representations or warranties that these products are free from patent, copyright, or mask work right infringement, unless otherwise specified.

Philips Semiconductors – a worldwide company

Argentina: see South America

Australia: 3 Figtree Drive, HOMEBUSH, NSW 2140, Tel. +61 2 9704 8141, Fax. +61 2 9704 8139 Austria: Computerstr. 6, A-1101 WIEN, P.O. Box 213,

Tel. +43 1 60 101 1248. Fax. +43 1 60 101 1210

Belarus: Hotel Minsk Business Center, Bld. 3, r. 1211, Volodarski Str. 6,

220050 MINSK, Tel. +375 172 20 0733, Fax. +375 172 20 0773

Belgium: see The Netherlands Brazil: see South America

Bulgaria: Philips Bulgaria Ltd., Energoproject, 15th floor,

51 James Bourchier Blvd., 1407 SOFIA, Tel. +359 2 68 9211, Fax. +359 2 68 9102

Canada: PHILIPS SEMICONDUCTORS/COMPONENTS,

Tel. +1 800 234 7381, Fax. +1 800 943 0087

China/Hong Kong: 501 Hong Kong Industrial Technology Centre,

72 Tat Chee Avenue, Kowloon Tong, HONG KONG, Tel. +852 2319 7888, Fax. +852 2319 7700

Colombia: see South America Czech Republic: see Austria

Denmark: Sydhavnsgade 23, 1780 COPENHAGEN V,

Tel. +45 33 29 3333, Fax. +45 33 29 3905 Finland: Sinikalliontie 3, FIN-02630 ESPOO, Tel. +358 9 615 800, Fax. +358 9 6158 0920

France: 7 - 9 Rue du Mont Valérien, BP317, 92156 SURESNES Cedex,

Tel. +33 1 4728 6600, Fax. +33 1 4728 6638

Germany: Hammerbrookstraße 69, D-20097 HAMBURG,

Tel. +49 40 2353 60, Fax. +49 40 2353 6300

Hungary: Philips Hungary Ltd., H-1119 Budapest, Fehervari ut 84/A,

Tel: +36 1 382 1700, Fax: +36 1 382 1800

India: Philips INDIA Ltd, Band Box Building, 2nd floor, 254-D, Dr. Annie Besant Road, Worli, MUMBAI 400 025,

Tel. +91 22 493 8541, Fax. +91 22 493 0966

Indonesia: PT Philips Development Corporation, Semiconductors Division. Gedung Philips, Jl. Buncit Raya Kav.99-100, JAKARTA 12510,

Tel. +62 21 794 0040 ext. 2501, Fax. +62 21 794 0080

Ireland: Newstead, Clonskeagh, DUBLIN 14, Tel. +353 1 7640 000, Fax. +353 1 7640 200

Israel: RAPAC Electronics, 7 Kehilat Saloniki St, PO Box 18053, TEL AVIV 61180, Tel. +972 3 645 0444, Fax. +972 3 649 1007

Italy: PHILIPS SEMICONDUCTORS, Via Casati, 23 - 20052 MONZA (MI),

Tel. +39 039 203 6838. Fax +39 039 203 6800

Japan: Philips Bldg 13-37, Kohnan 2-chome, Minato-ku, TOKYO 108-8507, Tel. +81 3 3740 5130, Fax. +81 3 3740 5057

Korea: Philips House, 260-199 Itaewon-dong, Yongsan-ku, SEOUL,

Tel. +82 2 709 1412, Fax. +82 2 709 1415

Malaysia: No. 76 Jalan Universiti, 46200 PETALING JAYA, SELANGOR,

Tel. +60 3 750 5214, Fax. +60 3 757 4880

Mexico: 5900 Gateway East, Suite 200, EL PASO, TEXAS 79905,

Tel. +9-5 800 234 7381, Fax +9-5 800 943 0087

Middle East: see Italy

Netherlands: Postbus 90050, 5600 PB EINDHOVEN, Bldg. VB,

Tel. +31 40 27 82785, Fax. +31 40 27 88399

New Zealand: 2 Wagener Place, C.P.O. Box 1041, AUCKLAND, Tel. +64 9 849 4160, Fax. +64 9 849 7811

Norway: Box 1, Manglerud 0612, OSLO. Tel. +47 22 74 8000, Fax. +47 22 74 8341

Pakistan: see Singapore

Philippines: Philips Semiconductors Philippines Inc., 106 Valero St. Salcedo Village, P.O. Box 2108 MCC, MAKATI, Metro MANILA, Tel. +63 2 816 6380, Fax. +63 2 817 3474

Poland: Al.Jerozolimskie 195 B, 02-222 WARSAW, Tel. +48 22 5710 000, Fax. +48 22 5710 001

Portugal: see Spain

Russia: Philips Russia, UI. Usatcheva 35A, 119048 MOSCOW,

Tel. +7 095 755 6918, Fax. +7 095 755 6919

Singapore: Lorong 1, Toa Payoh, SINGAPORE 319762,

Tel. +65 350 2538, Fax. +65 251 6500

Slovakia: see Austria Slovenia: see Italy

South Africa: S.A. PHILIPS Pty Ltd., 195-215 Main Road Martindale,

2092 JOHANNESBURG, P.O. Box 58088 Newville 2114,

Tel. +27 11 471 5401, Fax. +27 11 471 5398 South America: Al. Vicente Pinzon, 173, 6th floor,

04547-130 SÃO PAULO, SP. Brazil. Tel. +55 11 821 2333. Fax. +55 11 821 2382 Spain: Balmes 22, 08007 BARCELONA

Tel. +34 93 301 6312, Fax. +34 93 301 4107

Sweden: Kottbygatan 7, Akalla, S-16485 STOCKHOLM,

Tel. +46 8 5985 2000, Fax. +46 8 5985 2745 Switzerland: Allmendstrasse 140, CH-8027 ZÜRICH,

Tel. +41 1 488 2741 Fax. +41 1 488 3263

Taiwan: Philips Semiconductors, 5F, No. 96, Chien Kuo N. Rd., Sec. 1, TAIPEI, Taiwan Tel. +886 2 2134 2451, Fax. +886 2 2134 2874

Thailand: PHILIPS ELECTRONICS (THAILAND) Ltd.

60/14 MOO 11, Bangna Trad Road KM. 3, Bagna, BANGKOK 10260,

Tel. +66 2 361 7910, Fax. +66 2 398 3447

Turkey: Yukari Dudullu, Org. San. Blg., 2.Cad. Nr. 28 81260 Umraniye,

ISTANBUL, Tel. +90 216 522 1500, Fax. +90 216 522 1813

Ukraine: PHILIPS UKRAINE, 4 Patrice Lumumba str., Building B, Floor 7,

252042 KIEV, Tel. +380 44 264 2776, Fax. +380 44 268 0461

United Kingdom: Philips Semiconductors Ltd., 276 Bath Road, Hayes, MIDDLESEX UB3 5BX, Tel. +44 208 730 5000, Fax. +44 208 754 8421 United States: 811 East Arques Avenue, SUNNYVALE, CA 94088-3409,

Tel. +1 800 234 7381, Fax. +1 800 943 0087

Uruguay: see South America Vietnam: see Singapore

Yugoslavia: PHILIPS, Trg N. Pasica 5/v, 11000 BEOGRAD,

Tel. +381 11 3341 299, Fax.+381 11 3342 553

Internet: http://www.semiconductors.philips.com

For all other countries apply to: Philips Semiconductors,

Marketing Communications, Building BE-p, P.O. Box 218, 5600 MD EINDHOVEN, The Netherlands, Fax. +31 40 27 24825

© Philips Electronics N.V. 2001 SCA72

All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner.

The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent- or other industrial or intellectual property rights.

Printed in The Netherlands

613508/01/pp16

Date of release: 2001 Apr 04

Document order number: 9397 750 08067

Let's make things better.





